

# Memristor Presentation

Bailey Denzer

University of Minnesota, Morris

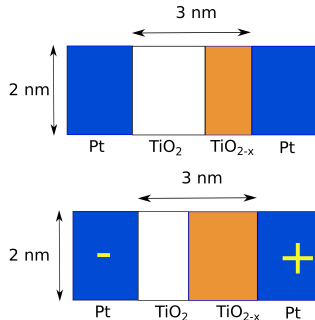
November 12 2015

# Outline

- 1 Introduction
- 2 Background
  - Memristor
  - Crossbar Array
- 3 Computation in Memory
  - Basic Design and IMP Logic
  - Results on Large Data Sets
- 4 Read/Write Models for a Memristor Based 1T1R Cell
- 5 Conclusion

# The Memristor

- Two-terminal, non-volatile device
- Made of resistant  $TiO_2$  and conductive  $TiO_{2-x}$
- Applying voltage alters the state



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# Comparison to Other Memories

Not shown in the chart:

- Memristors are potentially cheaper to manufacture than flash.
- DRAM energy shown does not account for refreshing.

Table 1 Comparison of data storage technologies. (Data drawn from public sources and HP internal research)

	Memristor	PCM	STT-RAM	DRAM	Flash	HD
Chip area per bit ( $F^2$ )	4	8–16	14–64	6–8	4–8	n/a
Energy per bit ( $pJ$ ) <sup>2</sup>	0.1–3	2–100	0.1–1	2–4	$10^4$ – $10^7$	$10^6$ – $10^7$
Read time (ns)	<10	20–70	10–30	10–50	25,000	$5$ – $8 \times 10^6$
Write time (ns)	20–30	50–500	13–95	10–50	200,000	$5$ – $8 \times 10^6$
Retention	>10 years	<10 years	Weeks	<Second	~10 years	~10 years
Endurance (cycles)	$\sim 10^{12}$	$10^7$ – $10^8$	$10^{15}$	$>10^{17}$	$10^3$ – $10^6$	$10^{15}$ ?
3D capability	Yes	No	No	No	Yes	n/a

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# Discussion

Questions?